

What is claimed is:

- 1 1. A semiconductor integrated circuit comprising a power supply  
2 wiring and a ground wiring and a decoupling capacitor formed  
3 between said power supply wiring and said ground wiring,  
4 wherein at least one of the electrodes of said decoupling  
5 capacitor consists of a shield layer formed in a plane shape  
6 on a semiconductor substrate, and said shield layer is  
7 connected electrically directly to the semiconductor  
8 substrate and is fixed to a power supply potential or the  
9 ground potential.
- 1 2. The semiconductor integrated circuit as claimed in claim  
2 1, wherein, out of the electrodes of said decoupling capacitor,  
3 the electrode opposing the electrode consisting of said shield  
4 layer consists of a wiring layer connected to wirings on the  
5 uppermost layer of a multilayer wiring structure via contact  
6 electrodes, and a capacitor insulating film for forming said  
7 decoupling capacitor is provided between said wiring layer  
8 and said shield layer.
- 1 3. A semiconductor integrated circuit comprising a power supply  
2 wiring and a ground wiring and a decoupling circuit formed  
3 between said power supply wiring and said ground wiring,  
4 wherein at least one electrode of said decoupling capacitor  
5 consists of a shield layer obtained by covering a plurality  
6 of protrusions formed on a semiconductor substrate, and said  
7 shield layer is electrically connected directly to the  
8 semiconductor substrate and is fixed to a power supply

9 potential or the ground potential.

1 4. The semiconductor integrated circuit as claimed in claim 3,  
2 wherein said protrusions are formed simultaneously with a  
3 gate electrode by the identical formation process for the  
4 gate electrode.

1 5. The semiconductor integrated circuit as claimed in claim 1  
2 or 3, wherein said decoupling capacitor is formed on an element  
3 isolation oxide film.

1 6. The semiconductor integrated circuit as claimed in claim 1  
2 or 3, wherein said shield layer consists of a silicon compound  
3 of a metal.